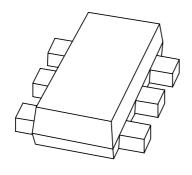
DISCRETE SEMICONDUCTORS

DATA SHEET



BC847BVN NPN/PNP general purpose transistor

Product data sheet Supersedes data of 2001 Aug 30 2001 Nov 07



NPN/PNP general purpose transistor

BC847BVN

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- · Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- Switch mode power supply complementary MOSFET driver
- · Complementary driver for audio amplifiers.

DESCRIPTION

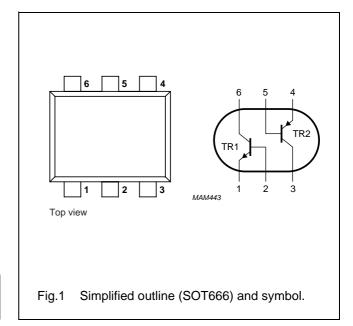
NPN/PNP transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BC847BVN	13

PINNING

PIN	DESCRIPTION				
1, 4	emitter	TR1; TR2			
2, 5	base	TR1; TR2			
6, 3	collector	TR1; TR2			



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	_	50	V		
V_{CEO}	collector-emitter voltage	open base	-	45	V		
V _{EBO}	emitter-base voltage	open collector	-	5	V		
I _C	collector current (DC)		-	100	mA		
I _{CM} peak collector current			_	200	mA		
I _{BM}	peak base current		_	200	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb} operating ambient temperature			-65	+150	°C		
Per device	•						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW		

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering is reflow soldering.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

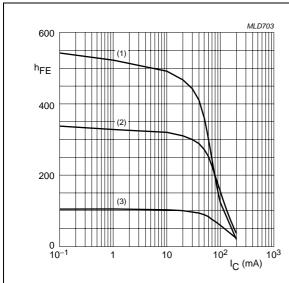
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity							
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	_	15	nA		
		V _{CB} = 30 V; I _E = 0; T _j = 150 °C	_	_	5	μΑ		
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA		
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA	200	_	450			
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 0.5 mA	_	_	100	mV		
	voltage	I _C = 100 mA; I _B = 5 mA; note 1	_	_	300	mV		
V _{BEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	_	755	_	mV		
f _T	transition frequency	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz	100	_	_	MHz		
NPN trans	istor							
V _{BE}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 2 mA	580	655	700	mV		
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1MHz$	_	_	1.5	pF		
C _e	emitter capacitance	$V_{EB} = 500 \text{ mV}; I_C = I_c = 0; f = 1MHz$	_	11	_	pF		
PNP trans	istor							
V_{BE}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	600	655	750	mV		
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_C = I_c = 0; f = 1MHz$	_	_	2.2	pF		
C _e	emitter capacitance	$V_{EB} = -500 \text{ mV}; I_E = I_e = 0; f = 1MHz$	_	10	_	pF		

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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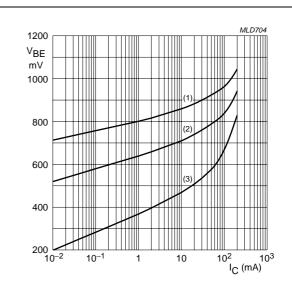
BC847BVN



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

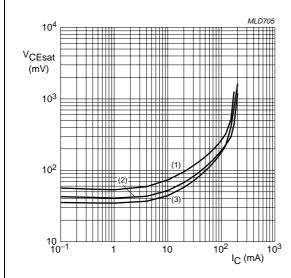
Fig.2 DC current gain as a function of collector current: typical values.



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

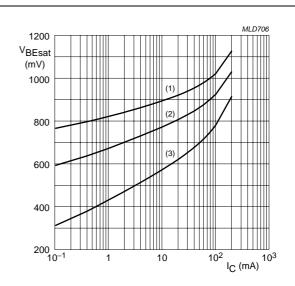
Fig.3 Base-emitter voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current: typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

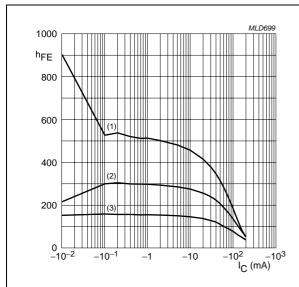
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Fig.5 Base-emitter saturation voltage as a function of collector current.

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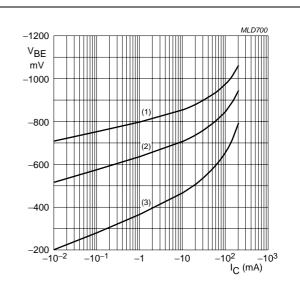
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TR2 (PNP); $V_{CE} = -5 \text{ V}$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

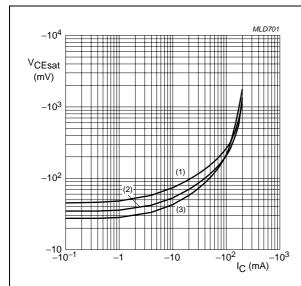
Fig.6 DC current gain as a function of collector current: typical values.



TR2 (PNP); $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

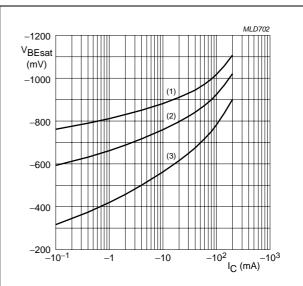
Fig.7 Base-emitter voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current: typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.9 Base-emitter saturation voltage as a function of collector current.

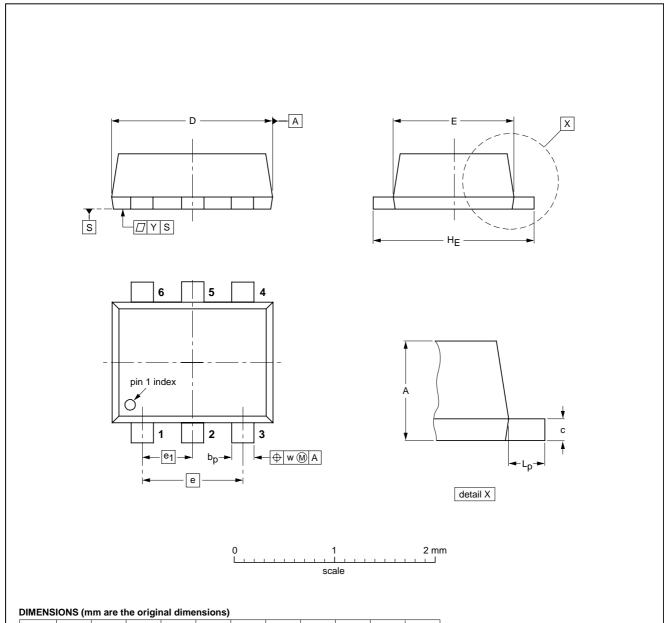
NPN/PNP general purpose transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENS	10143 (11	iiii are u	ie origii	iai uiiile	11510115)	
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UNIT	Α	bp	С	D	E	е	e ₁	HE	Lp	w	у
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						01-01-04 01-08-27

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
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